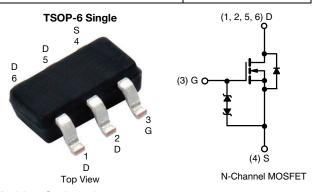
Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	60		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.042		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.063		
I <sub>D</sub> (A)	7		
Configuration	Single		



#### **FEATURES**

- TrenchFET® power MOSFET
- Typical ESD protection 800 V HBM
- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Material categorization:
   For definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

Marking	Code:	8Axxx		

ORDERING INFORMATION			
Package	TSOP-6		
Lead (Pb)-free and Halogen-free	SQ3426EEV-T1-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	60	.,	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	7		
	T <sub>C</sub> = 125 °C		4		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	6	Α	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	29		
Single Pulse Avalanche Current	L = 0.1 mH	l <sub>AS</sub>	10		
Single Pulse Avalanche Energy	L=0.1 min	E <sub>AS</sub>	5	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	5	W	
	T <sub>C</sub> = 125 °C		1.6		
Operating Junction and Storage Temperatu	re Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	R <sub>thJA</sub>	110	2000	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	30	°C/W	

#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. When mounted on 1" square PCB (FR-4 material).



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA		60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		-	2.5		
Coto Course Legisere		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V		-	-	± 500	nA	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V		=	-	± 1	mA	
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μА	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A	-	0.035	0.042	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.059	0.076		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 175 °C	-	0.074	0.095		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 4 A	-	0.057	0.063		
Forward Transconductance a	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 4 A	-	12	-	S	
Dynamic <sup>b</sup>					•			
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 30 V, f = 1 MHz	-	560	700	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	85	105		
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	55	70		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = 30 V, I <sub>D</sub> = 4 A	-	7.6	12		
Gate-Source Charge c	Q <sub>gs</sub>	V <sub>GS</sub> = 4.5 V		-	2.1	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	4.1	-		
Gate Resistance	Rg	f = 1 MHz		1.2	2.4	3.6	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	14		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, R_L = 7.5 \Omega$ $I_D \cong 4 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	12	18	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	19	29		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	7	11		
Source-Drain Diode Ratings and Charact	eristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	29	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.6 A, V <sub>GS</sub> = 0		_	0.75	1.2	V	

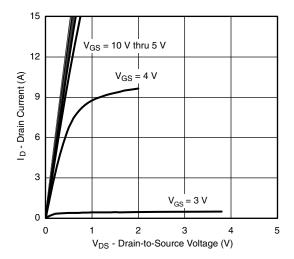
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

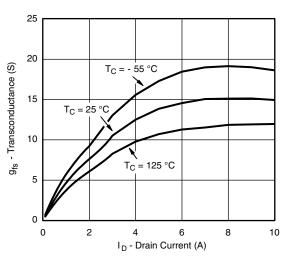
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



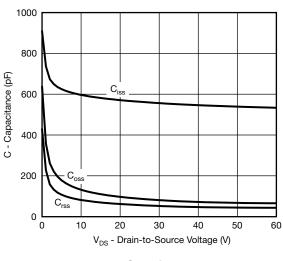
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



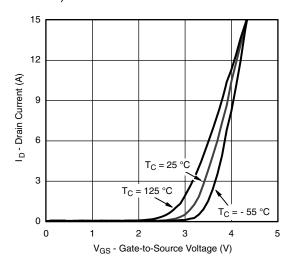
### **Output Characteristics**



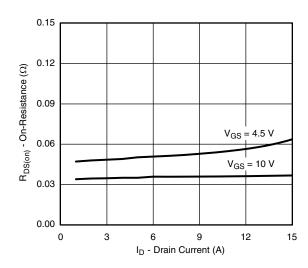
## Transconductance



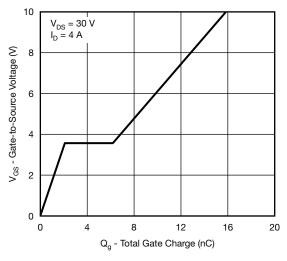
Capacitance



### **Transfer Characteristics**

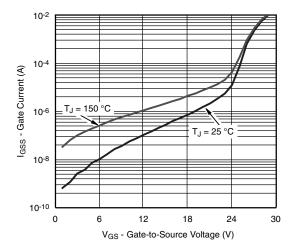


**On-Resistance vs. Drain Current** 

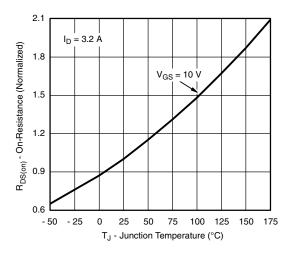




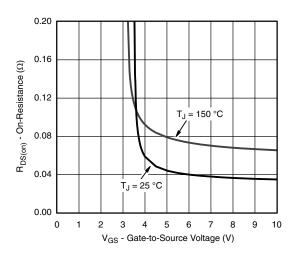
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



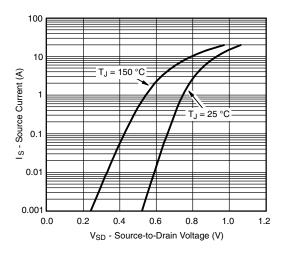
Gate Current vs. Gate-Source Voltage



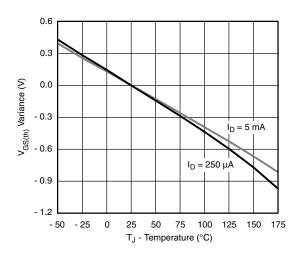
On-Resistance vs. Junction Temperature



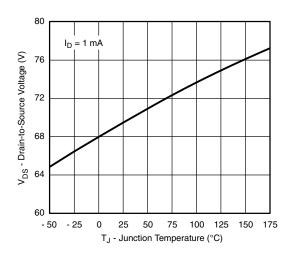
On-Resistance vs. Gate-Source Voltage



Source-Drain Diode Forward Voltage



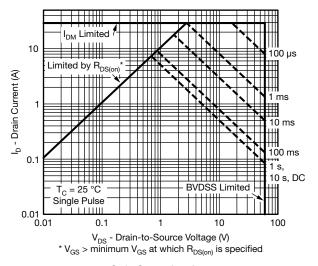
Threshold Voltage



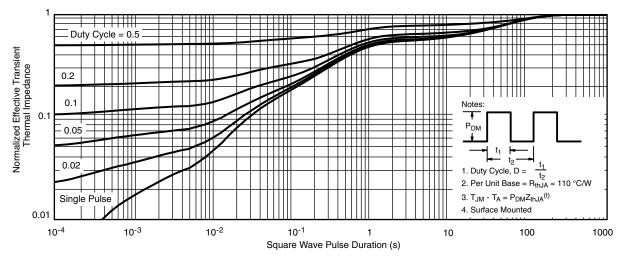
Drain-Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



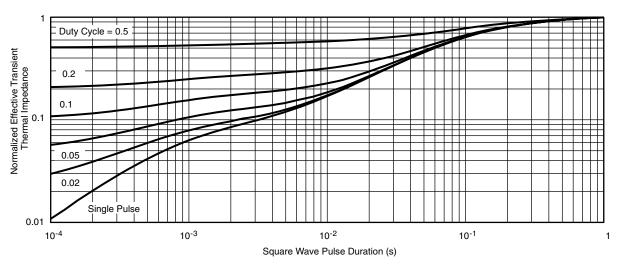
### Safe Operating Area



Normalized thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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